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(71)Applicant : SUMITOMO ELECTRIC IND LTD

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(72)Inventor : SHIMAZU MITSURU

(54) METHOD FOR GROWING III-V COMPOUND SEMICONDUCTOR CRYSTAL

(57)Abstract:

PURPOSE: To provide a method for growing a III-V compd. semiconductor crystal by which the thickness of a layer in which carbon has been doped at a high concn. can be controlled on an atomic layer level and highly uniform growth can be carried out even on a substrate of a large diameter.

CONSTITUTION: When a III-V compd. semiconductor crystal is grown by an organometallic vapor growth method, organometallic stock of a group III metal and organometallic stock of a group V metal are alternately fed and carbon is doped. If necessary, hydride of a group V metal is fed between the feeds of the stocks or added to the latter stock and fed; the amt. of the hydride fed and the feeding time are regulated and the amt. of carbon doped is controlled.

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